Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) An over-coating composition for coating a photoresist composition to provide a vertical photoresist pattern, said over-coating composition comprising (a) an over-coating resin derived from poly(acrylic acid / methyl acrylate), (b) a solvent, and (c) a basic compound.

2. (Original) The over-coating composition according to claim 1, wherein said over-coating resin is a water-soluble polymer.

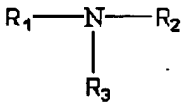
3. Cancelled.

4. (Original) The over-coating composition according to claim 1, wherein pKa of the conjugate acid of said basic compound is about 13 or less.

5. (Original) The over-coating composition according to claim 1, wherein said basic compound is a nitrogen containing compound.

6. (Previously Presented) The over-coating composition according to Claim 1, wherein said basic compound is selected from the group consisting of an amine compound and a hydroxide salt thereof; an amide compound; a urethane compound; and a mixture thereof.

7. (Original) The over-coating composition according to claim 6, wherein said amine compound is of the formula:



wherein each of R_1, R_2 and R_3 is independently H, or C_1-C_{20} alkyl.

8. (Original) The over-coating composition according to claim 7, wherein said alkyl is selected from the group consisting of unsubstituted C_1-C_{20} alkyl, C_1-C_{20} hydroxyalkyl, C_1-C_{20} alkyl carboxylic acid, C_1-C_{20} aminoalkyl, C_1-C_{20} alkylketone, and C_1-C_{20} alkylester.

9. (Original) The over-coating composition according to claim 6, wherein said amine compound is selected from the group consisting of L-proline, a tetraalkylammonium hydroxide salt, a tri(hydroxyalkyl)amine, and a mixture thereof.

10. (Original) The over-coating composition according to claim 9, wherein said tetraalkylammonium hydroxide salt is selected from the group consisting of tetramethylammonium hydroxide and tetramethylammonium hydroxide pentahydrate.

11. (Original) The over-coating composition according to claim 9, wherein said tri(hydroxyalkyl)amine is triethanolamine.

12. (Original) The over-coating composition according to claim 1, wherein the amount of said basic compound is in the range from about 0.001 to about 0.1 mol% of said solvent.

13. (Original) The over-coating composition according to claim 1, wherein the amount of said solvent is in the range from about 1000 to about 7000% by weight of said over-coating resin.

14.-21. Canceled

22. (Previously Presented) A composition for over-coating a photoresist layer used in a photolithography process wherein exposure of the photoresist to light of a particular wavelength generates acid from a photoacid generator present in the photoresist, said over-coating composition comprising (a) an over-coating resin derived from a mixture of acrylic

acid and an alkyl acrylate, (b) a solvent, and (c) a basic compound in an amount sufficient to diffuse into the underlying photoresist layer and neutralize at least a portion of the acid generated in the upper portion thereof.

23. (Previously Presented) The over-coating composition according to claim 22 wherein the amount of said basic compound is in the range from about 0.001 to about 0.1 mol% of said solvent.

24. (New) A process for forming a photoresist pattern, comprising the steps of:

(a) coating a photoresist composition on a substrate to form a photoresist film;

(b) coating an over-coating composition of claim 1 on the upper portion of said photoresist film to form a over-coating;

(c) exposing said over-coated substrate to light using a light source; and

(d) developing said exposed over-coated substrate.

25. (New) The process according to claim 24, wherein said photoresist composition comprises a chemically amplified photoresist resin.

26. (New) The process according to claim 25, wherein said chemically amplified photoresist resin is poly(tert-butyl bicyclo[2.2.1]hept-5-ene-2-carboxylate / 2-hydroxyethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate / bicyclo[2.2.1]hept-5-ene-2-carboxylic acid / maleic anhydride).

27. (New) The process according to claim 24 further comprising a baking step before and/or after said exposure step (c).

28. (New) The process according to claim 27, wherein said baking step is performed at a temperature range of from 10 to 200°C.

29. (New) The process according to claim 24, wherein said light source is ArF, KrF, F_2, EUV, E-beam, X-ray or ion beam.